风光欣技术资料

A1586

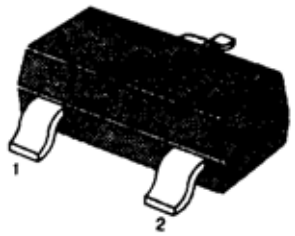
—PNP silicon —

■■**APPLICATION:**Audio Frequency General Purpose Amplifier Applications.

SOT-323

■■**MAXIMUM RATINGS**（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-150	mA
Collector Power Dissipation	P_C	100	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	－55~150	℃



1. Base 2. Emitter 3. Collector

■■**ELECTRICAL CHARACTERISTICS（Ta=25℃）**

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	70		700		V_{CE}= -6V，Ic= -2mA
Collector Cut-off Current	I_{CBO}			-0.1	μA	V_{CB}= -50V，I_E=0
Emitter Cut-off Current	I_{EBO}			-0.1	μA	V_{EB}= -5V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	-50			V	Ic= -0.1mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-50			V	Ic= -1mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	I_E= -0.1mA，Ic=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.1	-0.3	V	Ic= -100mA，I_B= -10mA
Gain bandwidth product	f_T	100	190		MHz	Ic= -10mA，V_{CE}= -5V
Common Base Output Capacitance	Cob		4	7	PF	V_{CB}= -10V, I_E=0, f = 1MHz
Noise Figure	N_F		1	10	dB	V_{CE}= -6V,Ic= -0.1mA,f= 1KHz,
						Rg= 10KΩ

■■h_{FE} **Classification And Marking**

Mark	SO	SY	SG	SL
Classification	O	Y	GR	BL
h_{FE}	70~140	120~240	200~400	350~700